

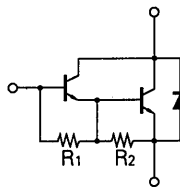
NPN SILICON EPITAXIAL TRANSISTOR
MP-3

DESCRIPTION

2SD1164-Z is designed for Low Frequency Amplifier and Switching, especially in Hybrid Integrated Circuits.

FEATURES

- High $h_{FE} = 2\ 000$ to $30\ 000$



$R_1 \approx 10\ k\Omega$
 $R_2 \approx 500\ k\Omega$

QUALITY GRADE

Standard

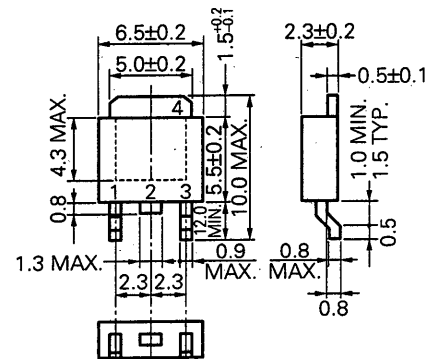
Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25\ ^\circ\text{C}$)

Collector to Base Voltage	V_{CBO}	150	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	8.0	V
Collector Current (DC)	I_C	2	A
Collector Current (Pulse)*	I_C	4	A
Total Power Dissipation ($T_a = 25\ ^\circ\text{C}$)**	P_T	2.0	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10\ ms$, Duty Cycle $\leq 50\ \%$

**When mounted on ceramic substrate of $7.5\ cm^2 \times 0.7\ mm$

PACKAGE DIMENSIONS
(in millimeters)

1. Base
2. Collector
3. Emitter
4. Collector

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

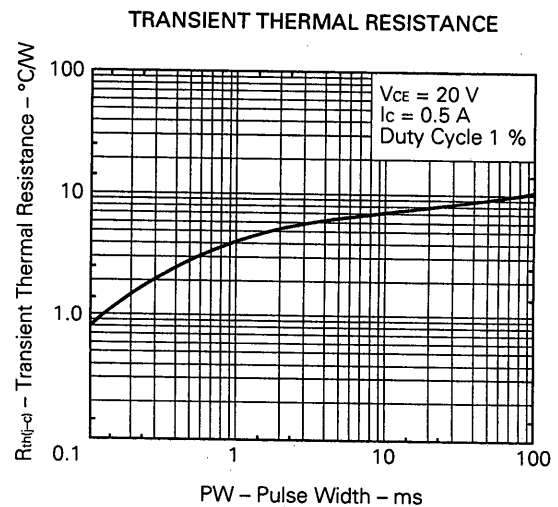
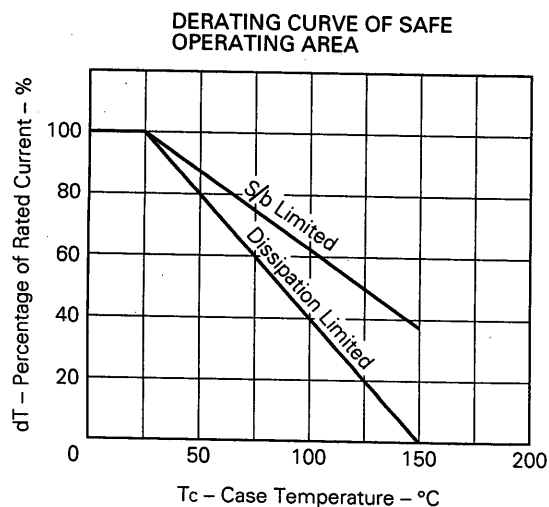
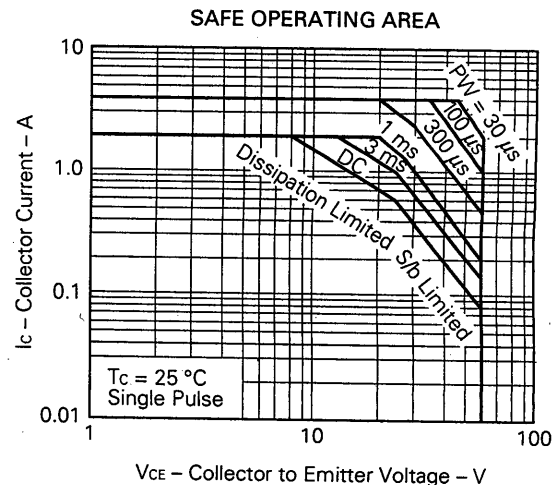
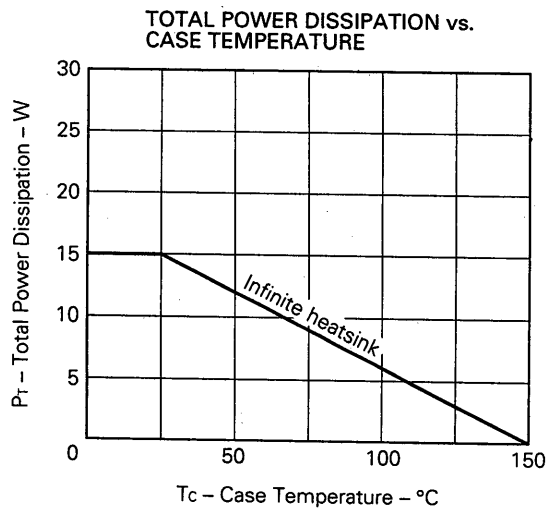
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			10	μA	$V_{CB} = 60\text{ V}, I_E = 0$
Emitter Cutoff Current	I_{EBO}			1.0	mA	$V_{EB} = 5.0\text{ V}, I_C = 0$
DC Current Gain	h_{FE1}^*	1 000				$V_{CE} = 2.0\text{ V}, I_C = 0.5\text{ A}$
DC Current Gain	h_{FE2}^*	2 000		30 000		$V_{CE} = 2.0\text{ V}, I_C = 1.0\text{ A}$
Collector Saturation Voltage	$V_{CE(sat)}^*$			1.5	V	$I_C = 1.0\text{ A}, I_B = 1.0\text{ mA}$
Base Saturation Voltage	$V_{BE(sat)}^*$			2.0	V	$I_C = 1.0\text{ A}, I_B = 1.0\text{ mA}$
Turn-on Time	t_{on}		0.5		μs	$I_C = 1.0\text{ A}, I_{B1} = -I_{B2} = 1.0\text{ mA}$ $V_{CC} \approx 50\text{ V}, R_L = 50\ \Omega$
Storage Time	t_{stg}		1.0		μs	
Fall Time	t_f		1.0		μs	

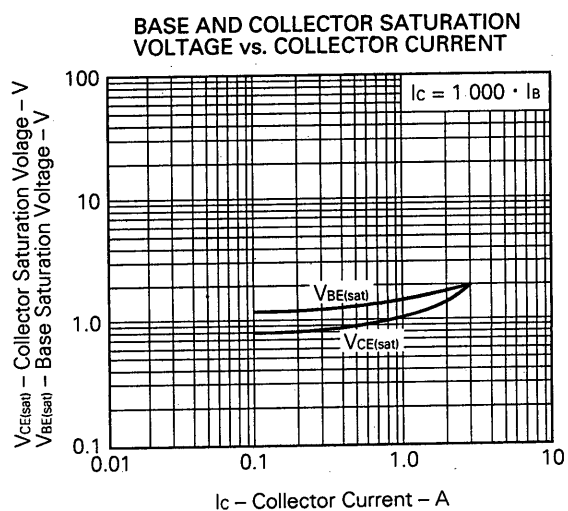
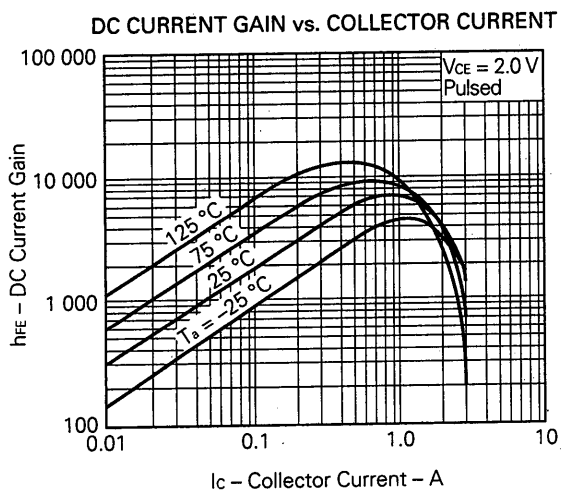
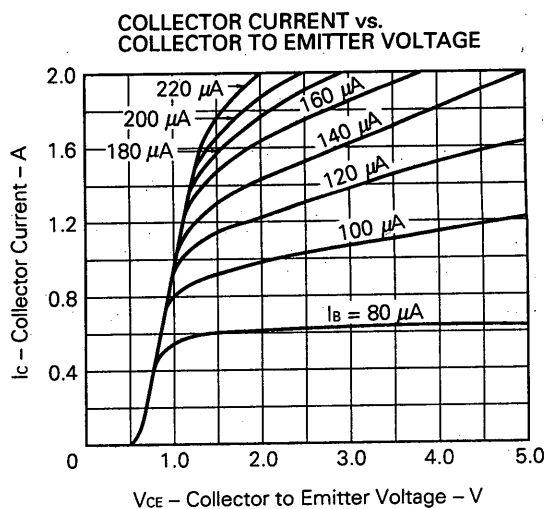
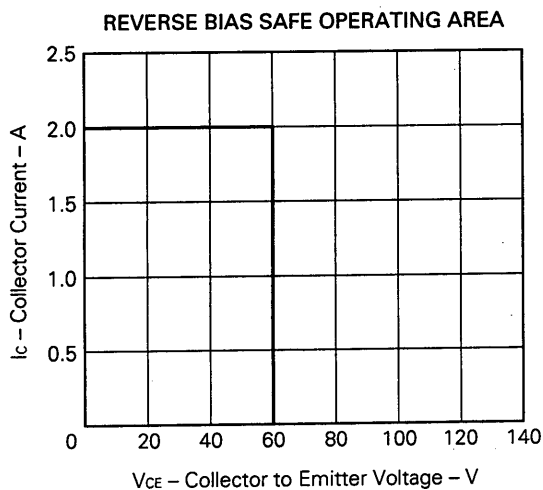
*Pulsed: $PW \leq 350\ \mu\text{s}$, Duty Cycle $\leq 2\%$

h_{FE} Classification

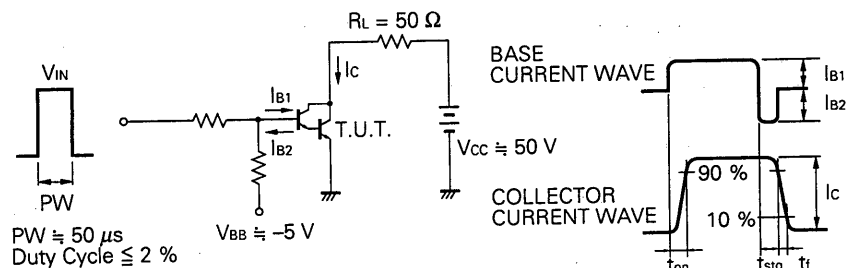
MARKING	M	L	K
h_{FE2}	2 000 to 5 000	4 000 to 10 000	8 000 to 30 000

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)





SWITCHING TIME (t_{on} , t_{stg} , t_f) TEST CIRCUIT



Reference

Application note name	No.
Quality control of NEC semiconductors devices.	TEI-1202
Quality control guide of semiconductors devices.	MEI-1202
Assembly manual of semiconductors devices.	IEI-1207
Design of Push-Pull Type Switching Regulators (Basic)	TEB-1002
Design of Push-Pull Type Switching Regulators (Applications)	TEB-1003
Optimum Base Drive Conditions of Switching Power Transistors	TEB-1014

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Application examples recommended by NEC Corporation.

Standard: Computer, Office equipment, Communication equipment, Test and Measurement equipment, Machine tools, Industrial robots, Audio and Visual equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Traffic control systems, Antidisaster systems, Anticrime systems, etc.